

BOM					
Prio rity leve	Specifications	Quan tity	Location number	Remark	
P	Capacitor, 0402 X7R 10nF ±10% 25V, C0402X7R103K250NY/T, EYANG	1	C17		
P	Capacitor, 1uF, ±10%, 10V, X5R, 0402, T=0. 5mm, CL05A105KP5NNNC, SAMSUNG	1	C911		
A	Capacitor, 1uF, ±10%, 10V, X5R, 0402, T=0. 5MM, GRM155R61A105KE15D, Murata				
P	Capacitor, 0805, X5R, 22uF, ±20%, 6. 3V (T=0. 85±0. 1MM), CL21A226MQCLRNC, SAMSUNG	1	C325		
P	Capacitor 0402 X5R 100nF ±10% 10V, C0402X5R104K100NY/T, EYANG	28	C101 C104 C107 C108 C112 C114 C115 C116 C118 C128 C150 C302 C312 C320 C511 C512 C523 C524 C702 C803 C804 C806 C824 C826 C827 C1001 C813 C109		
A	Capacitor CAP 100nF±10% 10V C0402, C1005X5R104KDT, DARFON				
P	Capacitor 0402 C0G 100pF ±5% 50V, C0402C0G101J500NY/T, EYANG	4	C502 C505 C508 C525		
A	Capacitor CAP 100pF±5% 50V, C0402, C1005NP0101JGT, DARFON				
P	Capacitor 0402 X7R 10nF ±10% 25V, C0402X7R103K250NY/T, EYANG	1	C809		
P	Capacitor 0402 C0G 18pF ±5% 50V, C0402C0G180J500NY/T, EYANG	1	C704		
P	Capacitor, 1. 0uF, ±10%, 6. 3V, X5R, 0402, T=0. 5mm, CL05A105KQ5NNNC, SAMSUNG	22	C14 C113 C117 C119 C120 C126 C129 C134 C135 C307 C308 C314 C316 C355 C404 C802 C808 C823 C1101 C1103 C1104 C1105		
A	Capacitor, 1uF, ±10%, 6. 3V, X5R, 0402, GRM155R60J105KE19D, Murata				
A	Capacitor 0402 X5R 1uF ±10% 6. 3V, C0402X5R105K6R3NT, EYANG				
P	Capacitor, 0603, X5R, 1uF±10%, H=0. 8MM, 25V, CL10A105KA8NNNC, SAMSUNG	6	C807 C329 C814 C815 C816 C817		
P	Capacitor 2. 2uF, ±20%, 6. 3V, X5R, 0402, CL05A225MQ5NNNC, SAMSUNG				

A	Capacitor 2.2uF, ±20%, 6.3V, X5R, 0402, C0402X5R225M6R3NT, EYANG	3	C111 C136 C1102	
A	Capacitor, 2.2uf, 0402, 6.3V, ±20%, C1005X5R225MCT, DARFON			
P	Capacitor, 0402 X7R 220pF ±10% 50V, C0402X7R221K500NY/T, EYANG	1	C701	
A	Capacitor, CAP 220pF±5% 50V, C0402, C1005NP0221JGT, DARFON			
P	Capacitor 0402 COG 22pF ±5% 50V, C0402COG220J500NY/T, EYANG	6	C600 C611 C612 C613 C614 C667	
A	Capacitor CAP 22pF±5% 50V, C0402, C1005NP0220JGT, DARFON			
P	Capacitor 0402 COG 33pF ±5% 50V, C0402COG330J500NY/T, EYANG	9	C15 C501 C503 C504 C506 C509 C510 C521 C522	
P	Electrical inductance, 39nH, ±5%, 0402, SDCL1005C39NJTDF, SUNLORD	1	C624	
P	Capacitor, 0402 COG 39pF ±5% 50V, C0402COG390J500NY/T, EYANG	1	C609	
P	Capacitor, 4.7uF, ±20%, 6.3V, X5R, 0402, CL05A475MQ5NRNC, SAMSUNG	7	C110 C401 C408 C409 C531 C801 C822	
P	Capacitor, 10uF, ±20%, 6.3V, X5R, 0603, CL10A106MQ8NNNC, SAMSUNG	2	C519 C520	
A	Capacitor, 10uF, ±20%, 6.3V, X5R, 0603, GRM188R60J106ME47D, MURATA			
A	Capacitor CAP 10UF±20% 6.3V C0603, C1608X5R106MCT, DARFON			
P	Capacitor, 56pF, ±5%, 50V, COG, 0402, C0402COG560J500NT, EYANG	1	C705	
P	Capacitor, 10uF, ±20%, 6.3V, X5R, 0603, CL10A106MQ8NNNC, SAMSUNG	7	C102 C103 C106 C301 C303 C306 C309	
A	Capacitor, 10uF, ±20%, 6.3V, X5R, 0603, GRM188R60J106ME47D, MURATA			
A	Capacitor CAP 10UF±20% 6.3V C0603, C1608X5R106MCT, DARFON			
P	Capacitor, 10uF, ±10%, 25V, X5R, 0805, T=1.25, CL21A106KAYNNNE, SAMSUNG	2	C820 C821	
P	Capacitor, 1206 X7R 1uf ±10% 50V (Y/T=1.25MM), CL31B105KBHNNNE, Samsung	1	C810	
P	Capacitor 0402 X5R 470nF ±10% 10V, C0402X5R474K100NY/T, EYANG	6	C684 C677 C675 C674 C676 C669	
A	Capacitor, CAP 470nF±10% 10V, C0402, C1005X5R474KDT, DARFON			
P	Capacitor 0402 COG 33pF ±5% 50V, C0402COG330J500NY/T, EYANG	1	C805	
P	Capacitor, 4.7uF, ±10%, 10V, X5R, 0603, T=0.8MM, CL10A475KP8NNNC, SAMSUNG	1	C811	

P	Resistor, 0 ohm, $\pm 5\%$, 1/16W, 0402, RC0402JR-070RL, YAGEO	14	R32 R42 R118 R119 R407 R409 R411 R419 R426 R501 R653 R656 R710 R711	
A	Resistor, 0 ohm, $\pm 5\%$, 1/16W, 0402, RC1005J000CS, SAMSUNG			
P	Resistor, 10K ohm, $\pm 5\%$, 1/16W, 0402, RC0402JR-0710KL, YAGEO	6	R9 R701 R804 R806 R807 R808	
P	Resistor, 33 ohm, $\pm 5\%$, 1/16W, 0402, RC0402JR-0733RL, YAGEO	1	R540	
P	Resistor, 1.5K ohm, $\pm 5\%$, 1/16W, 0402, RC0402JR-071K5L, YAGEO	4	R202 R512 R515 R516	
A	Resistor, 1.5K ohm, $\pm 5\%$, 1/16W, 0402, RC1005J152CS, SAMSUNG			
P	Resistor, 100K ohm, $\pm 1\%$, 1/16W, 0402, RC0402FR-07100KL, YAGEO	5	R813 R818 R819 R820 R541	
P	Resistor, 5.1 ohm, $\pm 5\%$, 1/10W, 0603, RC0603JR-075R1L, YAGEO	2	R811 C812	
P	Resistor, 16.9K ohm, $\pm 1\%$, 1/16W, 0402, RC0402FR-0716K9L, YAGEO	1	R1201	
P	Resistor, 1K ohm, $\pm 5\%$, 1/16W, 0402, RC0402JR-071KL, YAGEO	9	R312 R316 R511 R513 R514 R517 R704 R705 R712	
P	Resistor, 2.2K ohm, $\pm 5\%$, 1/16W, 0402, RC0402JR-072K2L, YAGEO	4	R204 R205 R206 R207	
A	Resistor, 2.2K ohm, $\pm 5\%$, 1/16W, 0402, RC1005J222CS, SAMSUNG			
P	Resistor, 240 ohm, $\pm 1\%$, 1/16W, 0402, RC0402FR-07240RL, YAGEO	2	R401 R404	
P	Resistor, 24K ohm, $\pm 1\%$, 1/16W, 0402, RC0402FR-0724KL, YAGEO	2	R702 R834	
P	Resistor, 27K ohm, $\pm 1\%$, 1/16W, 0402, RC0402FR-0727KL, YAGEO	1	R1202	
P	Resistor, 2K ohm, $\pm 5\%$, 1/16W, 0402, RC0402JR-072KL, YAGEO	1	R600	
A	Resistor, 2K ohm, $\pm 5\%$, 1/16W, 0402, RC1005J202CS, SAMSUNG			
P	Resistor, 3.3K ohm, $\pm 1\%$, 1/16W, 0402, RC0402FR-073K3L, YAGEO	1	R331	
A	Resistor, 3.3K ohm, $\pm 1\%$, 1/16W, 0402, RC1005F332CS, SAMSUNG			
P	Resistor, 75 ohm, $\pm 5\%$, 1/16W, 0402, RC0402JR-0775RL, Yageo	2	R815 R816	
P	Resistor 330K ohm, $\pm 1\%$, 1/16W, 0402, RC0402FR-07330KL, YAGEO	1	R329	
A	Resistor, 330K ohm, $\pm 1\%$, 1/16W, 0402, RC1005F334CS, SAMSUNG			

P	Resistor 39K ohm, ±1%, 1/16W, 0402, RC0402FR-0739KL, YAGEO	1	R324	
A	Resistor, 39K ohm, ±1%, 1/16W, 0402, RC1005F393CS, SAMSUNG			
P	Resistor, 470K ohm, ±5%, 1/16W, 0402, RC0402JR-07470KL, Yageo	1	R505	
P	Resistor, 470K ohm, ±1%, 1/16W, 0402, RC0402FR-07470KL, YAGEO	1	R814	
P	Resistor, 470 ohm, ±5%, 1/16W, 0402, RC0402JR-07470RL, YAGEO	2	R509 R510	
P	Resistor, 47K ohm, ±5%, 1/16W, 0402, RC0402JR-0747KL, YAGEO	2	R428 R506	
P	Resistor, 5.1K ohm, ±1%, 1/16W, 0402, RC0402FR-075K1L, YAGEO	2	R203 R8	
P	Resistor, 51 ohm, ±5%, 1/16W, 0402, RC0402JR-0751RL, YAGEO	2	R7 R10	
P	Resistor, 4.3K ohm, ±1%, 1/16W, 0402, RC0402FR-074K3L, YAGEO	1	R830	
P	Resistor, 68K ohm, ±1%, 1/16W, 0402, RC0402FR-0768KL, YAGEO	1	R817	
P	Resistor, 6.8K ohm, ±1%, 1/16W, 0402, RC0402FR-076K8L, YAGEO	1	R828	
P	Resistor, 8.2K ohm, ±5%, 1/16W, 0402, RC0402JR-078K2L, YAGEO	2	R402 R405	
P	Resistor, 100 ohm, ±5%, 1/16W, 0402, RC0402JR-07100RL, YAGEO	4	R211 R212 R11 R208	
P	Resistor, 0 ohm, ±5%, 1/10W, 0603, RC0603JR-070RL, YAGEO	1	R626	
P	Resistor, 0.22 ohm, ±1%, 1/4W, 0805, RL0805FR-07R22, YAGEO	1	R328	
A	Resistor, 0.22 ohm, ±1%, 1/4W, 0805, RUT2012FR22CS, SAMSUNG			
P	ESDpressure sensitiveResistor, 18V, 30pF, 0402, SDV1005E180C300NPTF, SUNLORD	29	T501 T502 T503 T504 T505 T506 T507 T508 T509 T510 T1201 T1215 T1216 T1217 T1218 T1219 T1220 T1301 T1302 T1303 T1304 T1305 T1306 T1307 T1308 T1312 T1313 T1204 T1205	
P	TVS, 5V, 1.0pF, DFN1006, ESD9N5BM-2/TR, WILL	2	T1202 T1203	
P	Power Electrical inductance, 10uH, ±20%, 4*4*1.8MM, 1.3A, SPH4040100METG DARFON	1	L801	
A	Power Electrical inductance, 10uH, ±20%, 4*4*1.8MM, 1.3A, SPH4018H100MT, Sunlord			
P	Power Electrical inductance, 10uH, ±20%, 3.0*3.0*1.0MM, 550mA, SWPA3010S100MT, Sunlord	1	L803	

P	Electrical inductance, 18nH, ±5%, 0402, SDCL1005C18NJTDF, Sunlord	1	L616	
P	Electrical inductance, 2. 2nH, ±0. 3nH, 0402, SDCL1005C2N2STDF, Sunlord	1	L618	
P	Electrical inductance, 0402, 2. 0nH±0. 3nH, I=300MA, RDC=0. 20ohmS DCL1005C2N0STF, Sunlord	1	L627	
P	Electrical inductance, 3. 0nH, ±0. 3nH, 0402, SDCL1005C3N0STDF, Sunlord	1	L622	
P	Electrical inductance, 4. 7nH, ±0. 3nH, 0402, SDCL1005C4N7STDF, Sunlord	2	L600 L619	
P	Electrical inductance, 6. 2nH, ±3%, 0402, SDCL1005C6N2FTDF, Sunlord	2	L623 L626	
P	Electrical inductance, 7. 5NH, ±5%, 0402, SDCL1005C7N5JTDF, Sunlord	1	L625	
P	Power Electrical inductance, 0. 68uH, ±30%, 2. 5*2. 0*1. 0mm, 2. 5A, MDMK2020TR68MM, TAIYO	2	L303 L301	
A	Power Electrical inductance, 0. 68uH, ±30%, 2. 5*2. 0*1. 0mm, 2. 5A, SPH252010HR68N, SUNLORD			
A	Power Electrical inductance, 0. 68uH, ±30%, 2. 5*2. 0*1. 0mm, 2. 5A, MGFL2520GR68MT-			
P	magnetic bead, 1K, 0402, BLM15BD102SN1D, Murata	8	B503 B504 B505 B506 B507 L502 B708 B709	
A	magnetic bead, 0402, 1000ohm/100MHZ, +/-25%, DCR:0. 95ohm, 200mA, SBJ100505T-102Y-			
A	magnetic bead, 1000R/100MHZ, I=200MA, RDC=1. 2ohm, 0402, FCM1005KF-102T02, TAI_TECH			
P	bilateral diode, BAV99, SOT-23, JCST	2	U1 U804	
P	LDO, 3. 3V, 300mA, SOT23-5, WL2801E33-5/TR, WILL	1	U805	
P	EMCP, 32Gb EMMC + 4Gb DDR2, 800MHZ, H9TP32A4GDCCPR-KGM, Hynix	1	U402	
A	EMCP,32Gb EMMC+4Gb DDR2,FBGA162,11.5*13*1.0mm,NLN04D04G,Acsip			
P	NMOS, 20V, 950mA, SOT-723, WNM2030-3/TR, WILL	1	Q301	
A	NMOS, 40V, 180mA, SOT-723, PNM723T703E0-2, SOT723, Prisemi			
P	charging transistor, PNP, PT236T30E2, PRISEMI	1	U303	
P	Level conversion IC, 3. 6*8. 6MM, SN74AVC32T245ZRLR, TI	1	U806	
P	Touch IC, QFN40, 5x5 x0. 8mm, GSL1688, Silead	1	U801	
P	DC - DC backlight driver IC, CP2123ST-A2, CHIPHOMER	1	U802	
P	1.2 MHz asynchronous booster type voltage regulator, TDFN, 2X2-6L, SGM6607YTDI6G/TR SGM	1	U803	

P	2G/3G Rf transceiver, TFBGA 11x11, 4.6mm*4.6mm, MT6166, MTK	1	U600	
P	MTK Power management, 5.8X5.8mm, MT6323, MTK	1	U301	
P	MTK Baseband chips, support WCDMA, qHD, 10.6x10.6x1.1, MT6572A/W, MTK	1	U101	
P	RF PA, FEM, Quad-Band, EDGE PA with Six Linear TRx Switch Ports and Dual-Band WCDMA, 6*6*1.0MM, SKY77590	1	U702	
P	Dual BALUN filter (GSM/DCS), RFBLN2012090BM5T25, HuaXinKe	1	Z600	
P	crystal, 26M, 7.5pF, 10ppm, 3.2mm×2.5mm, 7M260000028, TXC	1	X601	
A	26 MHZ crystal (3225), 7.4pF, ±10ppm, X1E000021043400, EPSON			
P	Schottky Barrier Diode, RB160M-40, JCST	1	D804	
P	Zener diode, 6.2V, 500mW, SIG3Z6V2T1G, SOD323, SIG	1	D803	
P	Zener diode, 18V, 500mW, SIG3Z18VT1G, SOD323, SIG	1	D802	
P	Zener diode, 5.1V, 500mW, SOD323, SIG3Z5V1T1G, SIG	1	D302	
A	Zener diode, 5.1V, 500mW, MM3Z5V1-2/TR, SOD323, will			
A	Zener diode, 5.1V, 500mW, PZ3D4V2H, SOD323, Prisemi			
P	Schottky Barrier Diode, 40V, 2A, RB060M-40, SOD-123, ROHM	1	D801	
A	Schottky Barrier Diode, 40V, 3A, PDS34W, SOD-123, PRISEMI			
P	PMOS, SIS2301LT1G, sig	1	QT700	
P	triode, 50V, 100mA, VMT3, PDTC143ZM, PRISEMI	1	Q801	
A	triode, 50V, 100mA, VMT3, DTC143ZM, ROHM			
P	main board PCB, P7_MAIN_V1.3, 4 layer HDI, Two makeup.No edge, texture FR4, makeup size:120.05*134.7*1.0MM, Bo min	1	PCB	
P	PUSH T Flash card PITCH 1.1, 8PIN, Size:15.2*14.1*1.85mm, CAF11-08193-S109, LCN	1	J1220	
P	The headset seat, 5PIN, Oblique KouChen plate, Size:12*6.3*4.2mm, AJK74-5K10006, SinGeen	1	J506	
A	The headset seat, 3.5MM, 5PIN, , Size:12*6.3*4.2mm JA0506360420-55, D_CHAIN			

P	MICRO USB, 5PIN, 0.65PITCH, 2.5MMH, 9.95x6.1x2.5MMH, MCB04-5K22010, SinGeen	1	J1202	
A	USB Micro Usb PTH0.65, 5PIN, Size:5.85*7.5*2.45mm UA0507065245-56, D_CHAIN			
P	Coaxial connector, Male head, 2*2*0.85mm, Fit height 1.5mm, 7.017A0-000-1R0, FAF	1	J301	
A	Coaxial connector, Male head, 2*2*0.85mm, Fit height 1.5mm, SCMJ-S00-001, Gigalane			
A	Coaxial connector, Male head, 2*2*0.85mm, Fit height 1.5mm, 20369-001E-01, I-PEX			
P	Coaxial switch, 3*3*1.75mm-6pin, C90P101-0000M-H, SPEEDTECH	1	J300	
A	Coaxial switch, 3*3*1.75mm-6pin, MM8430-2610RB3, Murata			
A	Coaxial switch, 3*3*1.75mm-6pin, C90-101-0004(E), SPEEDTECH			
A	Coaxial switch, 3*3*1.75mm-6pin, ECT818000001, ECT			
P	The side key switch, 5PINS, With pins, 4.6x3.5x1.8mm, SS304GS, Besttronics	4	S1 S1301 S1302 S1303	
A	The side key switch, 5PINS, With pins, 4.6x3.5x1.8mm, ST-1114RA, CRS			
P	ZIF attachments, 25PIN, BL125-25RL-TAGF, SCG	1	J1101	
A	ZIF attachments, 25pin, 9*3.5*1.0, PITCH0.6, FH26-25S-0.3SHW(05), HRS			
P	SIM card connector, 6PIN, 2.54PITCH, With a bridge with shelf, 16.30*16.40*1.5MM, CAF99-06153-SF27, LCN	1	J904	
A	SIM card connector, 6PINS, With a bridge with shelf, 16.3*16.4*1.5MMH, SIM04-6K22212, SinGeen			
A	SIM card connector, 6PINS, With a bridge with shelf, 2.54 PITCH, 16.3*16.4*1.5mmH, SIM04-6K33713, SinGeen			
P	Before the lock ZIF connectors, PTH0.5mm 30PIN, Size:19.4*5.85*1.5mm, AFC30-S30-F3A-HF, HeFeng	1	J801	
P	Before the lock ZIF connectors, PTH0.5mm 50PIN, Size: 29.4*5.8*1.5mm, AFC30-S50-F3A-HF, HeFeng	1	J803	
P	P7 Baseband shield, One-piece, the copper, P7_6572_BB_shield_V1	1		

P	P7 The RF shield, One-piece, the copper, P7 6572 RF shield V1	1		
P	P7 GPS shield, One-piece, the copper, P7 6572 GPS shield V1	1		
P	P7 PM shield, One-piece, the copper, p7-6572-pm-shield-v1	1		
P	P7 IC shield, One-piece, the copper, P7 6572 IC shield V2	1		
P	GPS LNA ,AR8159, Airoha	1	U1010	
P	SAW Filter for GPS, 1.35*1.05*0.6MM, SAFEB1G57KE0F00, Murata	1	U1005	
P	TCXO 2520 2.8V (26MHZ, 2 ppm), KT2520F26000ZAW18T8K, Kyocera	1	U1006	
A	TCXO, 26MHz (0.5PPM), 2520, TG5035CG-17N-26M, EPSON			
P	WIFI+BT+FM+GPS IC, QFN40, 5mm*5mm, MT6627N, MTK	1	U1000	
P	shrapnel, H:2.5MM, 3.5*1.5*2.5, CT-0025, Passo	4	ANT1 ANT2 ANT1003 ANT1004	
P	Capacitor, 0402 X5R 100nF $\pm 10\%$ 10V, C0402X5R104K100NY/T, EYANG	2	C1007 C1008	
A	Capacitor, CAP 100nF $\pm 10\%$ 10V C0402, C1005X5R104KDT, DARFON			
P	Capacitor, 0402 C0G 100pF $\pm 5\%$ 50V, C0402C0G101J500NY/T, EYANG	2	C1004 C1011	
A	Capacitor, CAP 100pF $\pm 5\%$ 50V, C0402, C1005NP0101JGT, DARFON			
P	Capacitor, 0402 X7R 10nF $\pm 10\%$ 25V, C0402X7R103K250NY/T, EYANG	1	C1002	
P	Capacitor, CAP 10pF ± 0.5 pF 50V, C0402, C1005NP0100DGT, DARFON	1	C1024	
P	Capacitor, 1uF, $\pm 10\%$, 10V, X5R, 0402, T=0.5mm, CL05A105KP5NNNC, SAMSUNG	2	C1012 C1022	
A	Capacitor, 1uF, $\pm 10\%$, 10V, X5R, 0402, T=0.5MM, GRM155R61A105KE15D, Murata			
P	Capacitor, 220nF, $\pm 20\%$, 10V, X5R, 0402, C0402X5R224M100NY/T, EYANG	1	C1010	
P	Capacitor, 0402 X7R 4.7nF $\pm 10\%$ 50V, C0402X7R472K500NY/T, EYANG	1	C1005	
P	Electrical inductance, 82nH, $\pm 5\%$, I=150MA, RDC=2.2ohm, 0402, SDCL1005C82NJTDF, SUNLORD	1	L1011	
P	Electrical inductance, 10nH, $\pm 5\%$, 0402, SDCL1005C10NJTDF, Sunlord	1	L1005	
P	Electrical inductance, 39nH, $\pm 5\%$, 0402, SDCL1005C39NJTDF, SUNLORD	2	L1004 R17	
P	Resistor, 0 ohm, $\pm 5\%$, 1/16W, 0402, 0402, RC0402JR-070RL, YAGEO	8	R1001 R1003 R1006 R1011 R1013 R1014 R15 R19	
A	Resistor, 0 ohm, $\pm 5\%$, 1/16W, 0402, RC1005J000CS, SAMSUNG			

P	Capacitor, 0402 X5R 100nF ±10% 10V, C0402X5R104K100NY/T, EYANG	2	C906 C907	
A	Capacitor, CAP 100nF±10% 10V C0402, C1005X5R104KDT, DARFON			
P	Capacitor, 2. 2uF, ±10%, 6. 3V, X5R, 0603, T=0. 8mm, CL10A225KQ8NNNC, SAMSUNG	1	C908	
P	Resistor, 2. 2K ohm, ±5%, 1/16W, 0402, RC0402JR-072K2L, YAGEO	1	R900	
A	Resistor, 2. 2K ohm, ±5%, 1/16W, 0402, RC1005J222CS, SAMSUNG			
P	Resistor, 20 ohm, ±1%, 1/16W, 0402, RC0402FR-0720RL, YAGEO	1	R901	
P	Acceleration sensor, 14bit, 2*2*1mm, DA213, miramems	1	U905	
P	Capacitor, 0402 X5R 100nF ±10% 10V, C0402X5R104K100NY/T, EYANG	2	C900 C901	
A	Capacitor, CAP 100nF±10% 10V C0402, C1005X5R104KDT, DARFON			
P	Capacitor, 0 ohm, ±5%, 1/16W, 0402, RC0402JR-070RL, YAGEO	1	R1	
A	Capacitor, 0 ohm, ±5%, 1/16W, 0402, RC1005J000CS, SAMSUNG			
P	magnetic bead, 1K, 0402, BLM15BD102SN1D, Murata	2	B501 B502	
A	magnetic bead, 0402, 1000ohm/100MHZ, +/-25%, DCR:0. 95ohm, 200mA, SBJ100505T-102Y-			
A	magnetic bead, 1000R/100MHZ, I=200MA, RDC=1. 2ohm, 0402, FCM1005KF-102T02, TAI_TECH			
P	Flash, IF=30MA, IFP=130MA, A-SL686W1D-A01-2T AMICC	1	D1101	
P	Resistor, 0 ohm, ±5%, 1/16W, 0402, RC0402JR-070RL, YAGEO	1	R1103	
A	Resistor, 0 ohm, ±5%, 1/16W, 0402, RC1005J000CS, SAMSUNG			

P	Capacitor, 1.0uF, ±10%, 6.3V, X5R, 0402, T=0.5mm, CL05A105KQ5NNNC, SAMSUNG	1	C16	
A	Capacitor, 1uF, ±10%, 6.3V, X5R, 0402, GRM155R60J105KE19D, Murata			
A	CAP 0402 X5R 1uF ±10% 6.3V, C0402X5R105K6R3NT, EYANG			
P	Resistor, 27 ohm, ±5%, 1/16W, 0402, RC0402JR-0727RL, YAGEO	2	R629 R630	
A	Resistor, 27 ohm, ±5%, 1/16W, 0402, RC1005J270CS, SAMSUNG			
P	Resistor, 36 ohm, ±5%, 1/16W, 0402, RC0402JR-0736RL, Yageo	1	R632	
A	Resistor, 36 ohm, ±5%, 1/16W, 0402, RC1005J360CS, SAMSUNG			
P	WCDMA RF PA, Band2, RF7241, RFMD	1	U707	
P	3G diplexer, WCDMA B2, SAYRF1G88CA0B0A, MURATA	1	U611	
P	Resistor, 0 ohm, ±5%, 1/16W, 0402, RC0402JR-070RL, YAGEO	1	R719	
A	Resistor, 0 ohm, ±5%, 1/16W, 0402, RC1005J000CS, SAMSUNG			
P	Capacitor, 0402 X5R 100nF ±10% 10V, C0402X5R104K100NY/T, EYANG	3	C671 C720 C722	
A	Capacitor, CAP 100nF±10% 10V C0402, C1005X5R104KDT, DARFON			
P	Capacitor, 0402 COG 18pF ±5% 50V, C0402COG180J500NY/T, EYANG	1	C725	
P	Electrical inductance, 8.2nH, ±5%, 0402, SDCL1005C8N2JTDF, Sunlord	1	C732	
P	Electrical inductance, 1.2nH, ±0.3nH, 0402, SDCL1005C1N2STDF, Sunlord	1	C726	
P	Capacitor, 0402 COG 4.3pF ±0.25pF 50V, C0420COG4R3C500NTB, EYANG	2	C662 C664	
P	Electrical inductance, 6.2nH, ±3%, 0402, SDCL1005C6N2FTDF, Sunlord	1	L601	
P	Electrical inductance, 2.7nH, ±0.3nH, 0402, SDCL1005C2N7STDF, Sunlord	1	C603	
P	Electrical inductance, 4.3nH, ±0.3nH, 0402, SDCL1005C4N3STDF, Sunlord	1	L614	
P	Resistor, 51 ohm, ±5%, 1/16W, 0402, RC0402JR-0751RL, YAGEO	1	R628	

P	PA, WCDMA band5 824M-849M, 3x3x1.0mm 10pin, RF7 248, RFMD	1	U708	
P	3G diplexer, WCDMA B5, SAYFH836MCA0F00R00, MURATA	1	U612	
A	3G diplexer, WCDMA B5, SAYFH836MCC0F0AR05, MURATA			
P	Resistor, 0 ohm, $\pm 5\%$, 1/16W, 0402, RC0402JR-070RL, YAGEO	1	C744	
A	Resistor, 0 ohm, $\pm 5\%$, 1/16W, 0402, RC1005J000CS, SAMSUNG			
P	Capacitor, 0402 X5R 100nF $\pm 10\%$ 10V, C0402X5R104K100NY/T, EYANG	2	C737 C740	
A	Capacitor, CAP 100nF $\pm 10\%$ 10V C0402, C1005X5R104KDT, DARFON			
P	Capacitor, 0402 X7R 1nF $\pm 10\%$ 50V, C0402X7R102K500NY/T, EYANG	1	C745	
A	Capacitor, CAP 1nF $\pm 10\%$ 50V, C0402, C1005X7R102KGT, DARFON			
P	Capacitor, 1uF, $\pm 10\%$, 10V, X5R, 0402, T=0.5mm, CL05A105KP5NNNC, SAMSUNG	1	C738	
A	Capacitor, 1uF, $\pm 10\%$, 10V, X5R, 0402, T=0.5MM, GRM155R61A105KE15D, Murata			
P	Electrical inductance, 22nH, $\pm 5\%$, 0402, SDCL1005C22NJTDF, Sunlord	1	C748	
P	Capacitor, 0402 COG 10pF ± 0.5 pF 50V, C0402COG100D500NY/T, EYANG	1	C660	
P	Capacitor, 56pF, $\pm 5\%$, 50V, COG, 0402, C0402COG560J500NT, EYANG	1	C733	
P	Capacitor, 82nF $\pm 20\%$ 10V, 0402, X5R, C0402X5R823M100NY/T EYANG	1	C736	
P	Electrical inductance, 1.0nH, ± 0.3 nH, , 0402, SDCL1005C1N0STDF, Sunlord	2	L658 L661	
P	Electrical inductance, 33nH, $\pm 5\%$, 0402, SDCL1005C33NJTDF, Sunlord	1	L612	
P	Electrical inductance, 5.1nH, ± 0.3 nH, 0402, SDCL1005C5N1STDF, Sunlord	1	L659	